## **CLAIM AMENDMENT**

Please CANCEL claims 2 and 3 without prejudice or disclaimer thereto.

Please AMEND claims 1 and 4-8, as follows.

Please ADD new claims 9-15, as follows.

1. (Currently Amended) A thin film transistor liquid crystal device (TFT LCD) device, comprising:

a substrate;



a thin film transistor formed on said substrate, having a source electrode and a drain electrode, wherein the drain electrode is formed of multiple layers comprising an uppermost layer formed of Cr or MoW;

an insulating layer formed over an entire surface of said substrate on which said thin film transistor is formed, and having a contact hole exposing a portion of the drain electrode; and

a pixel electrode <u>provided</u> corresponding to the thin film transistor, formed on said insulating layer and connected to the drain electrode through the contact hole,

wherein said pixel electrode is formed of a multi-layered conductive layer and comprises a lower layer formed of the same material as the uppermost layer of the multiple layers, and an upper layer of Al-containing metal.

- 2. (Cancelled)
- 3. (Cancelled)

4. (Currently Amended) The TFT LCD device-according to claim 2 1, wherein the multi-layered conductive layer is composed of a three layered conductive layer having a lower layer of same material as the uppermost layer of the multiple layers, an upper layer of Alecontaining metal, and pixel electrode further comprises an intermediate layer formed between the upper layer and the lower layer and formed of a material having a an electro-negativity that is in a middle level between that of the lower layer and that of the upper layer.



- 5. (Currently Amended) The TFT LCD device according to claim 2 1, wherein the multiple layers are composed of a three layered layer including further comprises a lower MoW layer formed of MoW and an intermediate Al-containing metal layer containing Al.
- 6. (Currently Amended) The TFT LCD device-according to claim 1, wherein said thin film transistor is a top-gate type polysilicon thin film transistor.
- 7. (Currently Amended) The TFT LCD device-according to claim 1, wherein said insulating layer is eomposed formed of a photo-sensitive organic insulating layer.
- 8. (Currently Amended) The TFT LCD device-according to claim 2 1, wherein further comprising a plurality of small projections that work as micro lens are formed on an upper surface of said insulating layer and works as micro lens.
  - 9. (New) A thin film transistor liquid crystal device (TFT LCD), comprising: a substrate;

a thin film transistor formed on said substrate, having a source electrode and a drain electrode, wherein the drain electrode is formed of Cr or MoW;

an insulating layer formed over said thin film transistor, and having a contact hole exposing a portion of the drain electrode; and

a pixel electrode provided corresponding to the thin film transistor, formed on said insulating layer and connected to the drain electrode through the contact hole,

wherein said pixel electrode is a multi-layered conductive layer and comprises a lower layer formed of the same material as the drain electrode.

- 10. (New) The TFT LCD of claim 9, wherein the pixel further comprises an upper layer formed of metal containing Al.
- 11. (New) The TFT of claim 9, wherein the pixel electrode further comprises an intermediate layer formed between the upper layer and the lower layer and formed of a material having an electro-negativity that is between that of the lower layer and that of the upper layer.
- 12. (New) The TFT LCD according to claim 9, wherein the drain electrode further comprises a lower layer formed of MoW and an intermediate metal layer containing Al.
- 13. (New) The TFT LCD according to claim 9, wherein said thin film transistor is a top-gate type polysilicon thin film transistor.

14. (New) The TFT LCD according to claim 9, wherein said insulating layer is formed of a photo-sensitive organic insulating layer.

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15. (New) The TFT LCD according to claim 9, further comprising a plurality of small projections formed on an upper surface of said insulating layer and works as micro lens.